NSN 5961-01-199-0383

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No



View Online at https://aerobasegroup.com/nsn/5961-01-199-0383

Inclosure Material:
Metal
Overall Length:
1.573 inches
Overall Height:
0.500 inches
Overall Width:
1.050 inches
Function For Which Designed:
Switching
Mounting Facility Quantity:
2
Internal Configuration:
Field effect
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case and quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
500.0 drain to source voltage and 500.0 drain to gate voltage
Current Rating Per Characteristic:
4.50 amperes source current and 7.00 amperes off-state current, peak
Power Rating Per Characteristic:
75.0 watts total power dissipation
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius ambient air
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 unthreaded hole and 1 case
Specification Data:
81349-mil-s-19500/542 government specification
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:

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